N-Channel Enhancement Mode Field Effect Transistor

Product Summary

- ǒ V_{DS} 60V
- ǒ I_D 350mA
- ǒ $R_{DS(ON)}$(at V_{GS}=10V) 1.0q
- ǒ $R_{DS(ON)}$(at V_{GS}=4.5V) 1.4q

General Description

- ǒ Trench Power MV MOSFET technology
- ǒ Voltage controlled small signal switch
- ǒ Low input Capacitance
- ǒ Fast Switching Speed
- ǒ Low Input / Output Leakage
- ǒ Moisture Sensitivity Level 1
- ǒ Epoxy Meets UL 94 V-0 Flammability Rating
- ǒ Halogen Free

Applications

- ǒ Battery operated systems
- ǒ Solid-state relays
- ǒ Direct logic-level interface TTL/CMOS

ƴ **Absolute Maximum Ratings** (T_A=25 unless otherwise noted)

Parameter	Symbol	Limit	Unit

Drainƴ **Electrical Characteristics** (T_J=25 unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
Static Parameter						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}= 0V, I_D=250εA	60	-	-	V

Zero Gate VoltageHeaderƿ193.25 759.1 50.1

B V

Figure 13. Maximum Transient Thermal Impedance

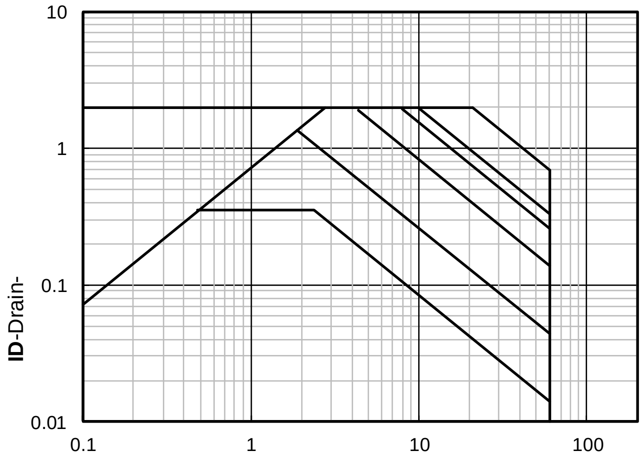


Figure 14. Safe Operation Area

ƴ Test Circuits & Waveforms

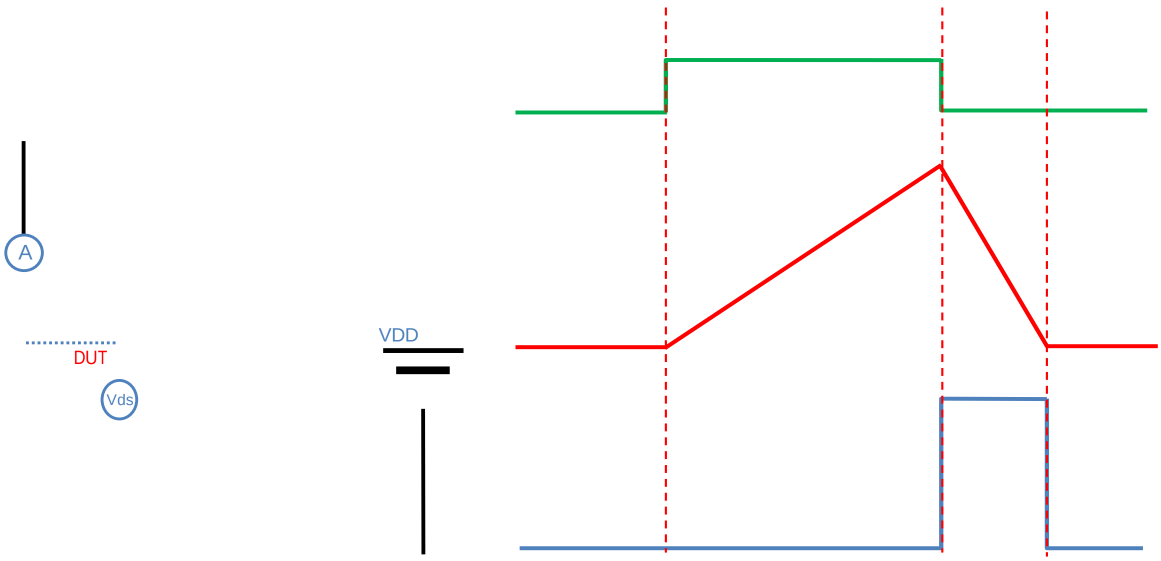
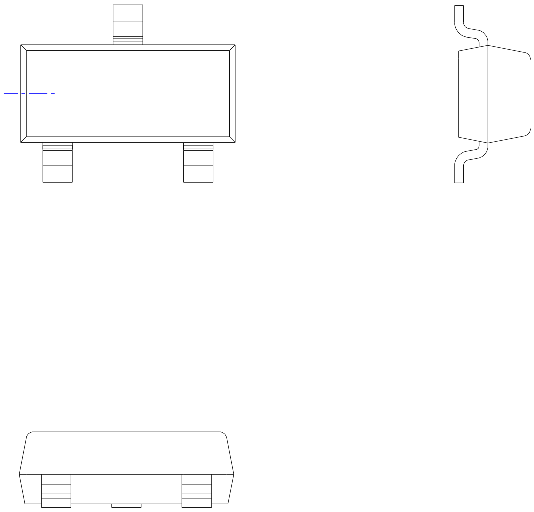


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

√ SOT-23 Package information



UNITÖ mm